

Important notice

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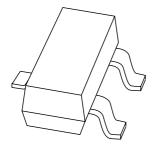
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BSR13; **BSR14**NPN switching transistors

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 13



NPN switching transistors

BSR13; **BSR14**

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

• Switching and linear applications.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complements: BSR15 and BSR16.

MARKING

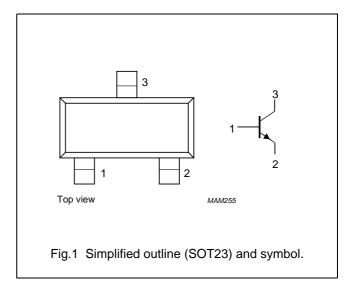
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSR13	U7*
BSR14	U8*

Note

- 1. * = p: Made in Hong Kong.
 - * = t : Made in Malaysia.
 - * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE				
NUMBER	NAME	DESCRIPTION	VERSION		
BSR13	_	plastic surface mounted package; 3 leads			
BSR14					

NPN switching transistors

BSR13; BSR14

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BSR13		_	60	V
	BSR14		_	75	V
V _{CEO}	collector-emitter voltage	open base			
	BSR13		_	30	V
	BSR14		_	40	V
V _{EBO}	emitter-base voltage	open collector			
	BSR13		_	5	V
	BSR14		_	6	V
I _C	collector current (DC)		_	800	mA
I _{CM}	peak collector current		_	800	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current				
	BSR13	I _E = 0; V _{CB} = 50 V	_	30	nA
		I _E = 0; V _{CB} = 50 V; T _j = 150 °C	_	10	μΑ
	collector cut-off current				
	BSR14	I _E = 0; V _{CB} = 60 V	_	10	nA
		$I_E = 0$; $V_{CB} = 60 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	10	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V			
	BSR13		_	30	nA
	BSR14		_	10	nA

^{1.} Transistor mounted on an FR4 printed-circuit board.

NPN switching transistors

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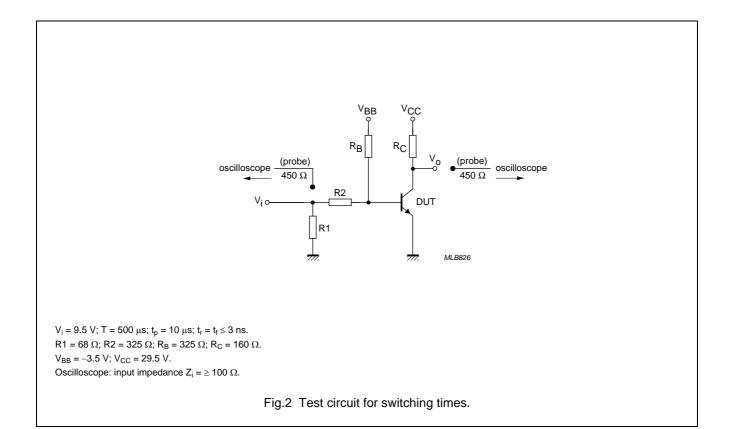
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
h _{FE}	DC current gain	I _C = 0.1 mA; V _{CE} = 10 V; note 1	35	_	
		I _C = 1 mA; V _{CE} = 10 V; note 1	50	_	
		I _C = 10 mA; V _{CE} = 10 V; note 1	75	_	
		I _C = 150 mA; V _{CE} = 10 V; note 1	100	300	
		I _C = 150 mA; V _{CE} = 1 V; note 1	50	_	
	DC current gain	I _C = 500 mA; V _{CE} = 10 V; note 1			
	BSR13		30	_	
	BSR14		40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA			
	BSR13		_	400	mV
	BSR14		_	300	mV
	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA			
	BSR13		_	1.6	V
	BSR14		_	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA			
	BSR13		_	1.3	V
	BSR14		0.6	1.2	V
	base-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA			
	BSR13		_	2.6	V
	BSR14		_	2	V
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	8	pF
f _T	transition frequency	I _C = 20 mA; V _{CE} = 20 V;			
	BSR13	f = 100 MHz	250	_	MHz
	BSR14		300	_	MHz
Switching t	imes (between 10% and 90% levels); see Fig.2	1	-	
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	_	35	ns
t _d	delay time	$I_{Boff} = -15 \text{ mA}$	_	15	ns
t _r	rise time	1	_	20	ns
t _{off}	turn-off time	1	_	250	ns
t _s	storage time	1	_	200	ns
t _f	fall time	1	_	60	ns

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN switching transistors

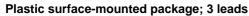
BSR13; BSR14



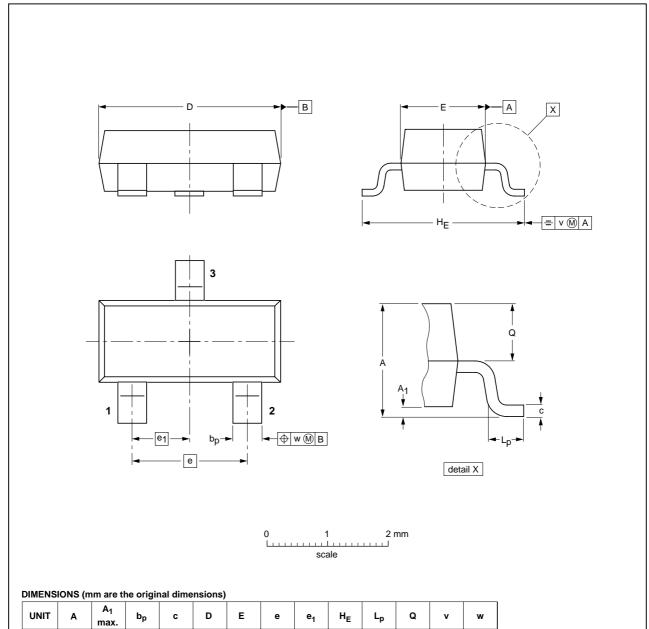
NPN switching transistors

BSR13; BSR14

PACKAGE OUTLINE



SOT23



OUTLINE	LINE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				04-11-04 06-03-16
						06-03-

1.9

0.95

0.45

0.55

0.2

0.1

2004 Jan 13 6

0.48

0.38

0.9

NPN switching transistors

BSR13; **BSR14**

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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